

## TRANSISTOR(NP)

### FEATURES

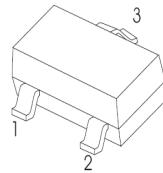
- High Collector-Emitter Voltage
- Complement to MMBTA94

### MARKING: 3D

### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	500	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_c$	Collector Current	100	mA
$P_c$	Collector Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	357	°C/W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55~+150	°C

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1. BASE
2. Emitter
3. Collector

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>Collector-base breakdown voltage</b>	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	500			V
<b>Collector-emitter breakdown voltage</b>	$V_{(BR)CEO}^*$	$I_C=1\text{mA}, I_B=0$	400			V
<b>Emitter-base breakdown voltage</b>	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
<b>Collector cut-off current</b>	$I_{CBO}$	$V_{CB}=400\text{V}, I_E=0$			0.1	$\mu\text{A}$
<b>Emitter cut-off current</b>	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$			0.1	$\mu\text{A}$
<b>DC current gain</b>	$h_{FE(1)}^*$	$V_{CE}=10\text{V}, I_C=1\text{mA}$	40			
	$h_{FE(2)}^*$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	50		200	
	$h_{FE(3)}^*$	$V_{CE}=10\text{V}, I_C=50\text{mA}$	45			
	$h_{FE(4)}^*$	$V_{CE}=10\text{V}, I_C=100\text{mA}$	40			
<b>Collector-emitter saturation voltage</b>	$V_{CE(sat)1}^*$	$I_C=1\text{mA}, I_B=0.1\text{mA}$			0.4	V
	$V_{CE(sat)2}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.5	V
	$V_{CE(sat)3}^*$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.75	V
<b>Base-emitter saturation voltage</b>	$V_{BE(sat)}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.75	V
<b>Collector output capacitance</b>	$C_{ob}$	$V_{CB}=20\text{V}, I_E=0, f=1\text{MHz}$			7	pF
<b>Emitter input capacitance</b>	$C_{ib}$	$V_{EB}=0.5\text{V}, I_C=0, f=1\text{MHz}$			130	pF

\*Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .